

Application No. 10/702,440  
Response to Office Action dated February 6, 2006

**Amendment to the Claims:**

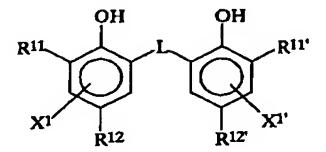
This listing of claims will replace all prior versions, and listing, of claims in the application:

**Listing of Claims:**

What is claimed is:

1. (currently amended) A photothermographic material containing, on a substrate, at least a photosensitive silver halide having an average particle size of 5 nm to 40nm, a non-photosensitive organic silver salt comprising silver behenate in an amount of 40 mol% to 99 mol%, a reducing agent which contains a compound represented by general formula (R):

**General formula (R)**



in which R<sup>11</sup> and R<sup>11'</sup> each represents independently an alkyl group of 1 to 20 carbon atoms, R<sup>12</sup> and R<sup>12'</sup> each represents independently an alkyl group of 1 to 20 carbon atoms, L represents an -S- group or -CHR<sup>13</sup>- group, R<sup>13</sup> represents a hydrogen atom or an alkyl group of 1 to 20 carbon atoms, and X<sup>1</sup> and X<sup>1'</sup> each represents independently a hydrogen atom or a group capable of substitution on a benzene ring,  
and

a binder in which the total silver iodide content of the photosensitive silver halide is 90 mol% to 100 mol%, and the coating amount of photosensitive silver halide in terms of an amount of silver is 0.005 g/m<sup>2</sup> to 0.05 g/m<sup>2</sup> wherein in the photosensitive silver halide is formed in a state where the non-photosensitive organic salt is not

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present and wherein the average  $\gamma$  -phase ratio of the photosensitive silver halide is 5 mol% to 90 mol%.

2. (cancelled)

3. (cancelled)

4. (cancelled)

5. (cancelled)

6. (cancelled)

7. (cancelled)

8. (currently amended) A photothermographic material according to claim 1 7 , wherein  $R^{11}$  and  $R^{11'}$  in the general formula (R) each represents independently a secondary or tertiary alkyl group of 3 to 15 carbon atoms.

9. (original) A photothermographic material according to claim 1, which further comprising a compound represented by the following general formula (H):

General formula (H)

$Q-(Y)_N-C(Z_1)(Z_2)X$

in which Q represents an alkyl group, aryl group or heterocyclic group, Y represents a bivalent connection group, N represents 0 or 1,  $Z_1$  and  $Z_2$  each represents a halogen

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atom, and X represents a hydrogen atom or an electron attractive group.

10. (currently amended) An image forming method for a photothermographic material which comprises exposing a photothermographic material according to claim claims 1 by using a semiconductor laser having an emission peak intensity at a wavelength of from 350 nm to 450 nm as a light source.

11. (cancelled)

12. (cancelled)

13. (previously presented) A photothermographic material according to claim 1, wherein the average  $\gamma$ -phase ratio of the photosensitive silver halide is 25 mol% to 50 mol%.

14. (original) A photothermographic material according to claim 1, further comprising a compound in which a one-electron oxidant formed by one-electron oxidation can release one electron or more electrons.

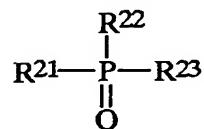
15. (cancelled)

16. (previously presented) A photothermographic material according to claim 1, wherein the non-photosensitive organic silver salt contains silver behenate in an amount of 65 mol% to 85 mol%.

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18. (original) A photothermographic material according to claim 1, further comprising a compound represented by the following general formula (D):

General formula (D)



in which R<sup>21</sup> to R<sup>23</sup> each represents independently an alkyl group, aryl group, alkoxy group, aryloxy group, amino group or heterocyclic group.

19. (original) An image forming method for a photothermographic material according to claim 10, wherein the exposure illuminance of the semiconductor laser is 1 mW/mm<sup>2</sup> or more.

20. (previously presented) An image forming method for the photothermographic material according to claim 10, wherein the exposure illuminance of the semiconductor laser is 10 mW/mm<sup>2</sup> to 50 mW/mm<sup>2</sup>.